Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	114267	esd electrostatic	USPAT	OR	OFF	2005/11/15 10:59
L2	568	1 same (internal adj (block unit units circuit))	USPAT	OR	OFF	2005/11/15 11:17
L3	167	2 same ( diode or (diode adj connected))	USPAT	OR	OFF	2005/11/15 11:17
L4	101	3 same (vcc vdd vss gnd ground)	USPAT	OR	OFF	2005/11/15 11:03
L5	93	4 same protect\$5	USPAT	OR	OFF	2005/11/15 11:04
L6	47	5 same power	USPAT	OR	OFF	2005/11/15 11:14
L7	10	6 same second	USPAT	OR	OFF	2005/11/15 11:14
L8	58	5 same (source supply)	USPAT	OR	OFF	2005/11/15 11:14
L9	17	8 same second	USPAT	OR .	OFF	2005/11/15 11:14
L10	11	9 not 7	USPAT	OR	OFF	2005/11/15 11:14
L11	567	1 same (internal adj circuit)	USPAT	OR	OFF	2005/11/15 11:21
L12	0	2 same (diode adj connected adj (transistor fet nmos pmos mosfet))	USPAT	OR	OFF	2005/11/15 11:19
L13	48	1 same (diode adj connected adj (transistor fet nmos pmos mosfet))	USPAT	OR	OFF	2005/11/15 11:18
L14	3	2 same ( connected adj (transistor fet nmos pmos mosfet))	USPAT	OR	OFF	2005/11/15 11:29
L15	10	13 same second	USPAT	OR	OFF	2005/11/15 11:20
L16	9	1 same (second adj internal adj circuit)	USPAT	OR	OFF	2005/11/15 11:28
L17	157	(second adj internal adj circuit)	USPAT	OR	OFF.	2005/11/15 11:28
L18	1	17 same ( diode adj4 (transistor fet nmos pmos mosfet))	USPAT	OR	OFF	2005/11/15 11:30
L19	36	17 same ((transistor fet nmos pmos mosfet))	USPAT	OR .	OFF	2005/11/15 11:31
L20	4	19 same 1	USPAT	OR	OFF	2005/11/15 11:31